

P-Channel Enhancement Mode Power MOSFET

Description

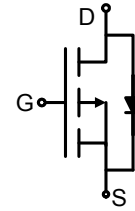
The HM4453B uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

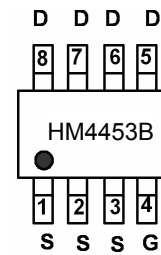
- $V_{DS} = -12V, I_D = -9A$
 $R_{DS(ON)} < 45m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 30m\Omega @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

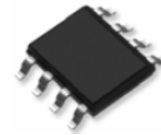
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOP-8 top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM4453B	HM4453B	SOP-8	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current -Continuous	I_D	-9	A
Drain Current -Pulsed ^(Note 1)	I_{DM}	-27	A
Maximum Power Dissipation	P_D	1.8	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	69	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-12	-	-	V

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.45	-0.65	-1.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-9A	-	19	30	mΩ
		V _{GS} =-2.5V, I _D =-5A	-	26	45	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-9A		17	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-6V, V _{GS} =0V, F=1.0MHz	-	1100	-	PF
Output Capacitance	C _{oss}		-	390	-	PF
Reverse Transfer Capacitance	C _{rss}		-	300	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-6V, I _D =-1A , R _L =6Ω, V _{GEN} =-4.5V, R _g =6Ω	-	25	-	nS
Turn-on Rise Time	t _r		-	45	-	nS
Turn-Off Delay Time	t _{d(off)}		-	72	-	nS
Turn-Off Fall Time	t _f		-	60	-	nS
Total Gate Charge	Q _g	V _{DS} =-6V, I _D =-9A, V _{GS} =-4.5V	-	11.5	-	nC
Gate-Source Charge	Q _{gs}		-	1.5	-	nC
Gate-Drain Charge	Q _{gd}		-	3.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-1.0A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	9	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

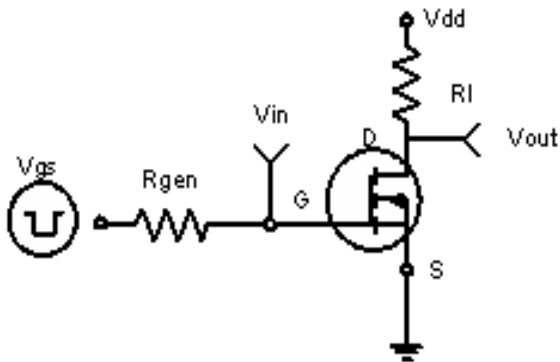


Figure 1: Switching Test Circuit

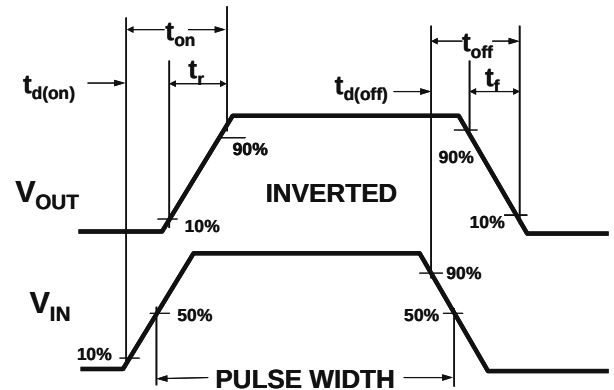


Figure 2: Switching Waveforms

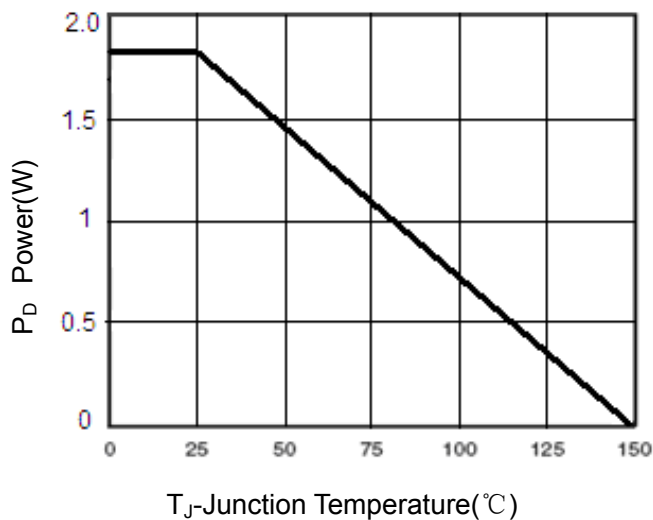


Figure 3 Power Dissipation

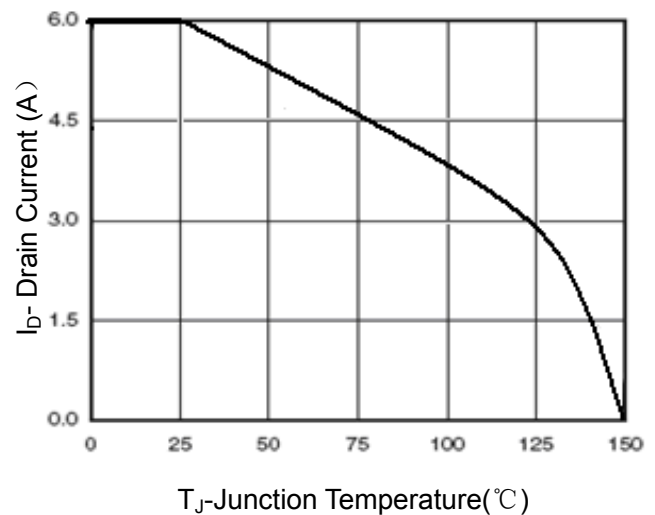


Figure 4 Drain Current

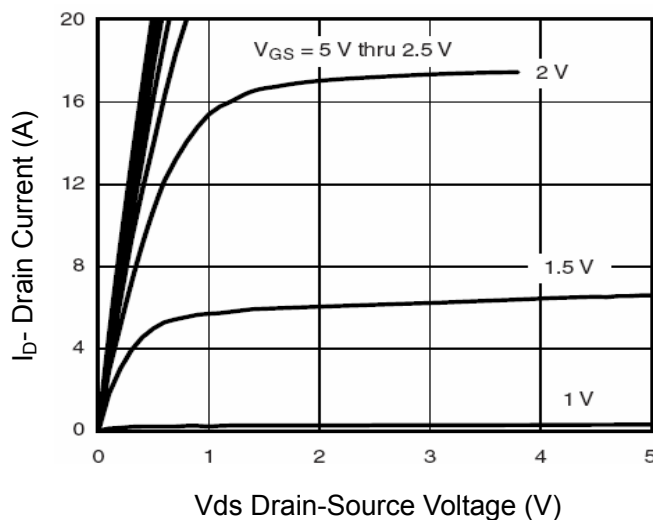


Figure 5 Output Characteristics

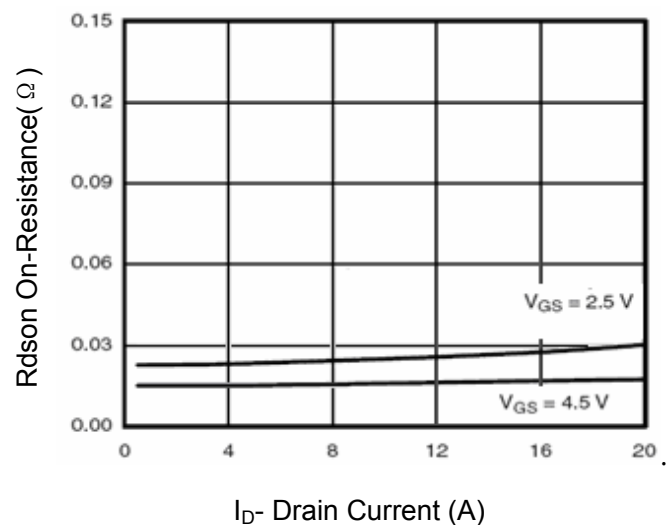


Figure 6 Drain-Source On-Resistance

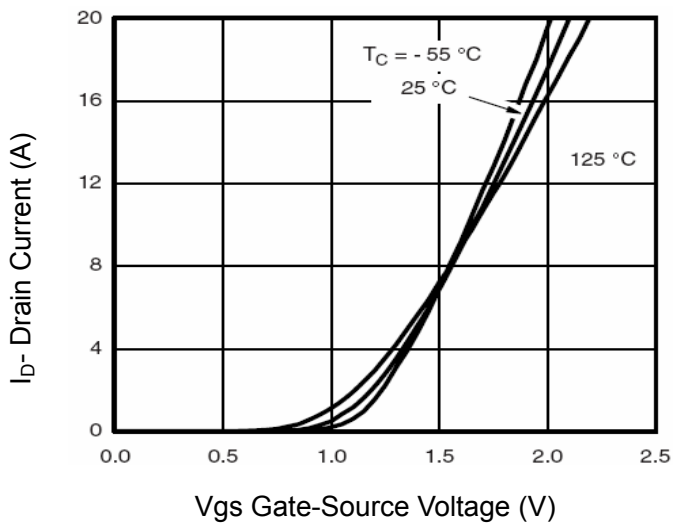


Figure 7 Transfer Characteristics

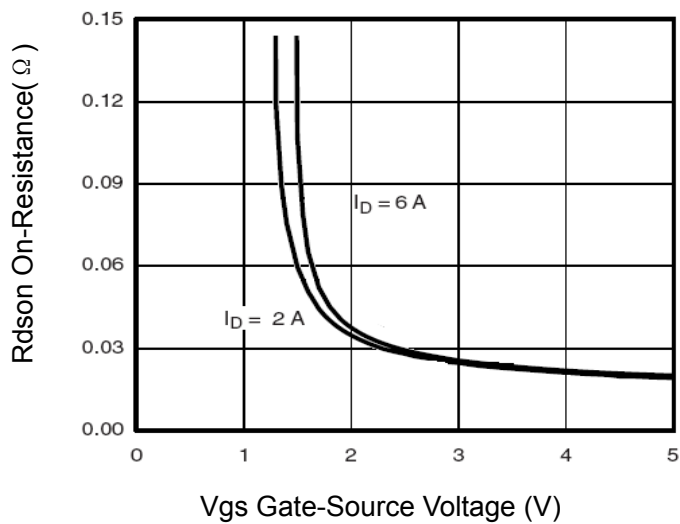


Figure 9 $R_{DS(on)}$ vs V_{GS}

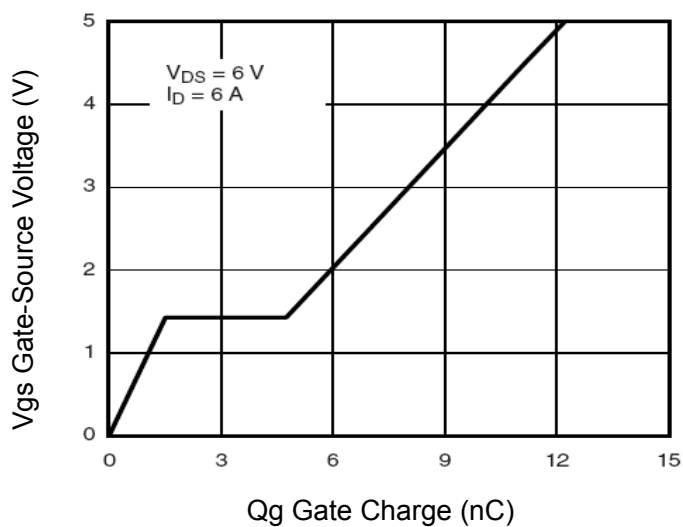


Figure 11 Gate Charge

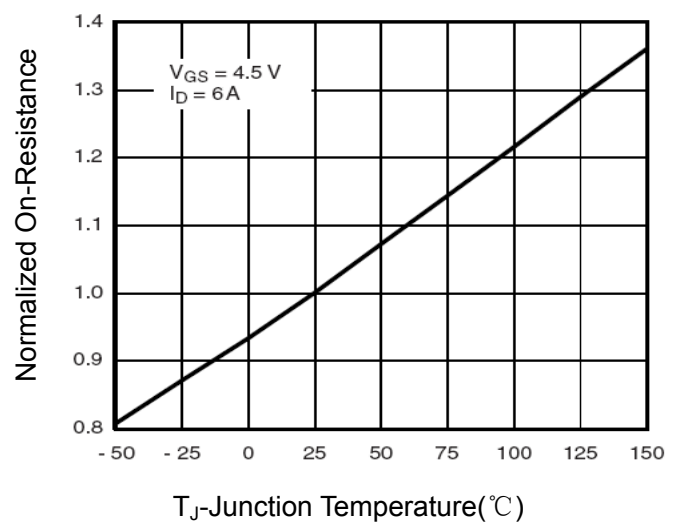


Figure 8 Drain-Source On-Resistance

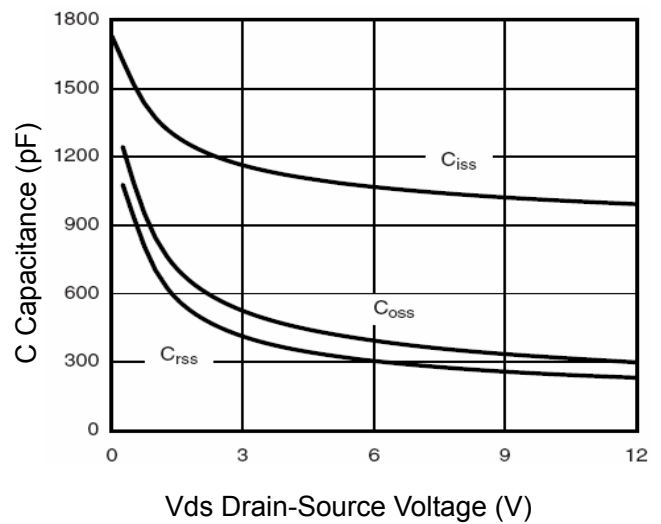


Figure 10 Capacitance vs V_{DS}

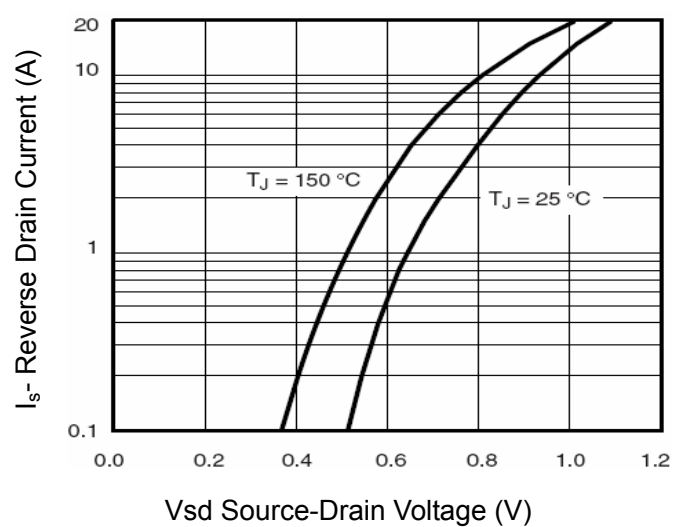


Figure 12 Source- Drain Diode Forward

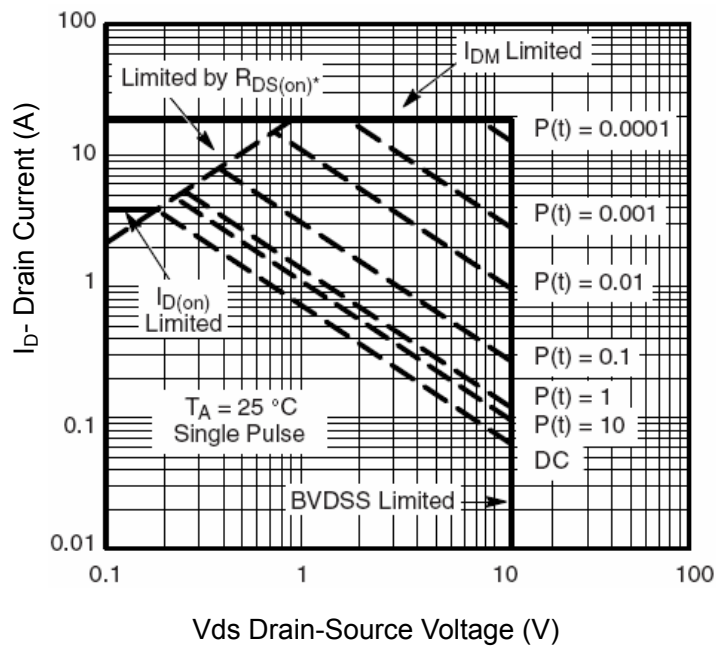


Figure 13 Safe Operation Area

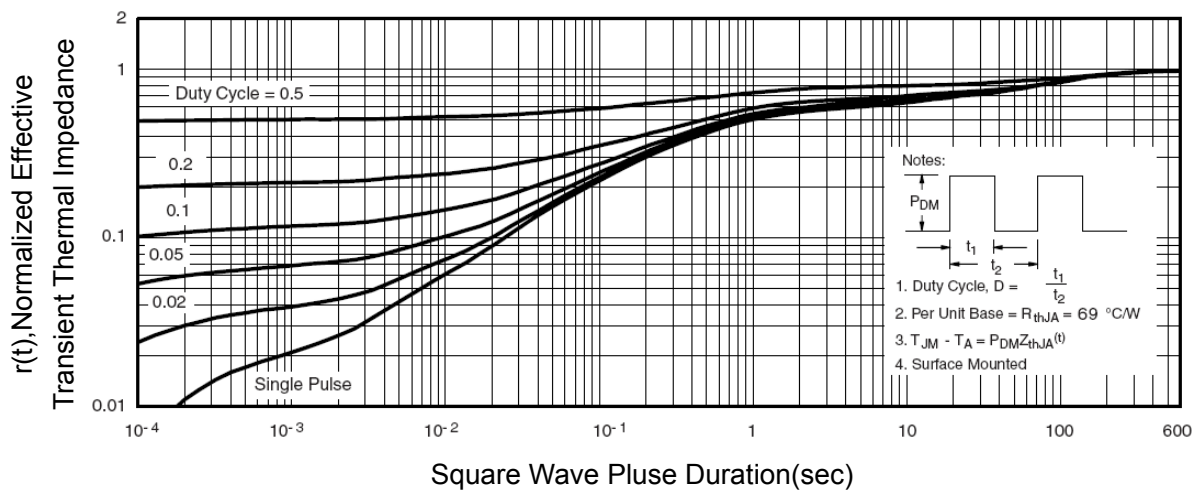
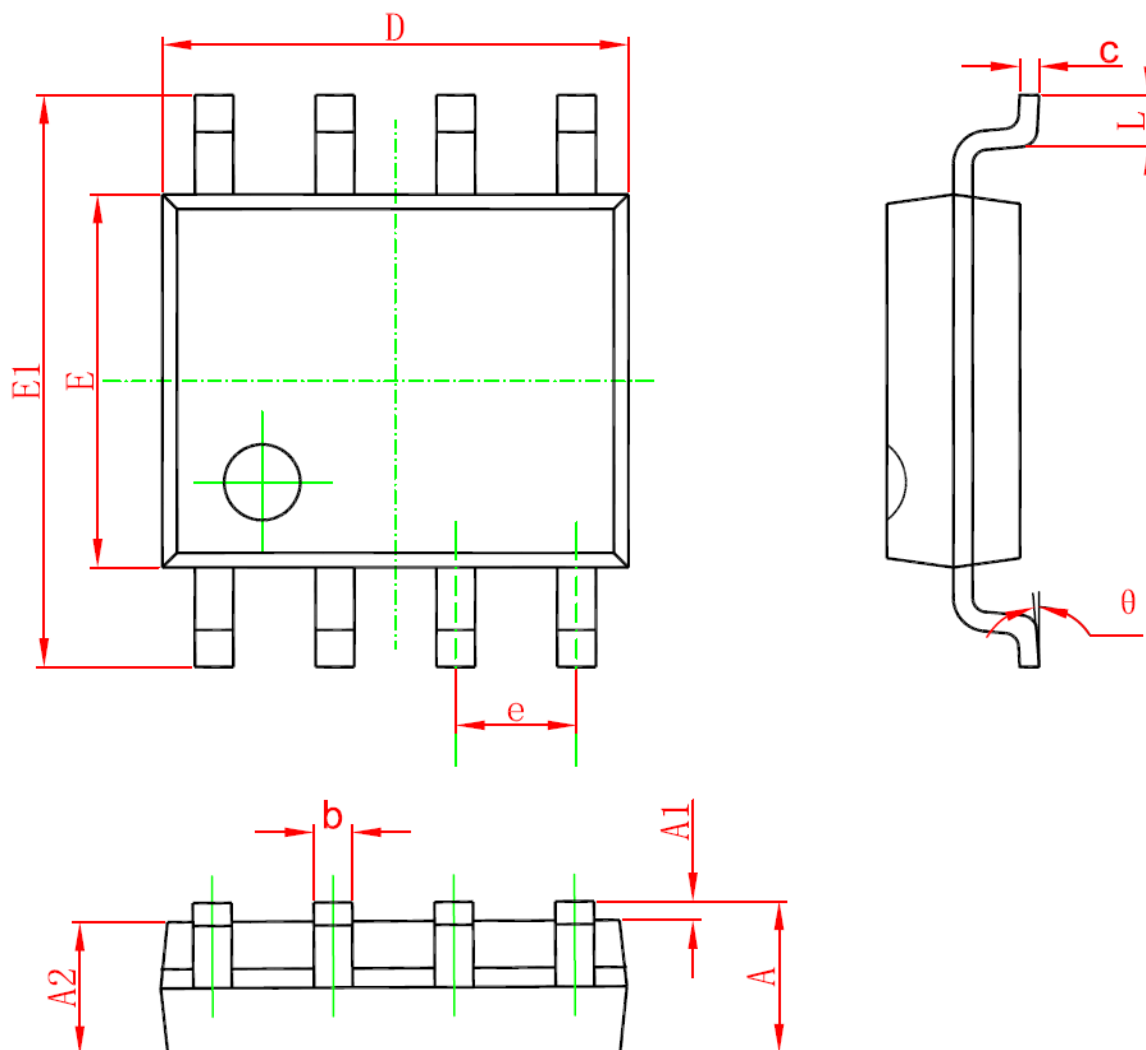


Figure 14 Normalized Maximum Transient Thermal Impedance

SOP-8 PACKAGE IN FORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°